

Electronic Supplementary Information (ESI)

**Novel Green Phosphorescence from Pristine ZnO Quantum Dot: Tuning of
Correlated Color Temperature**

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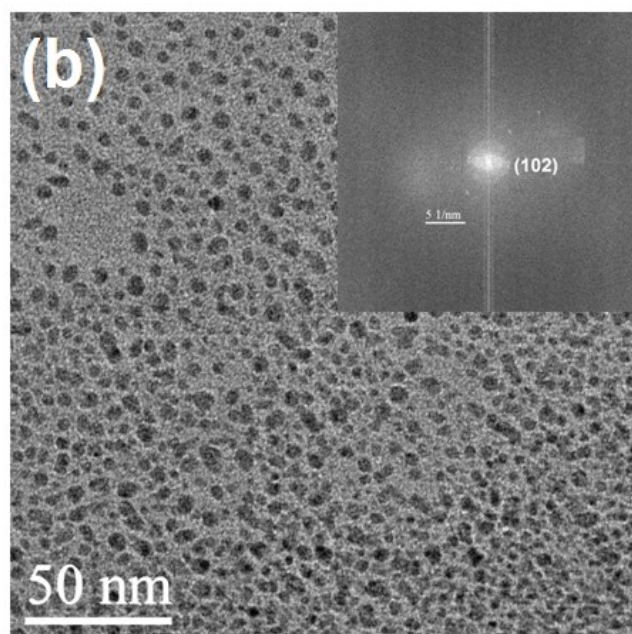
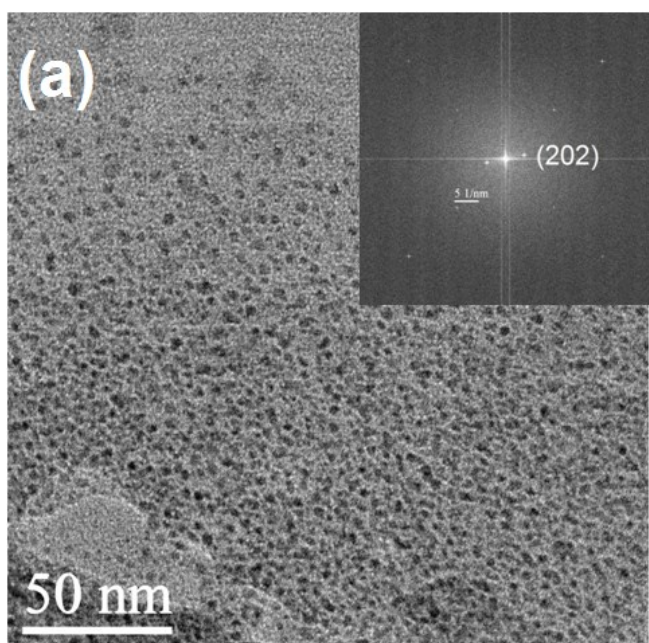
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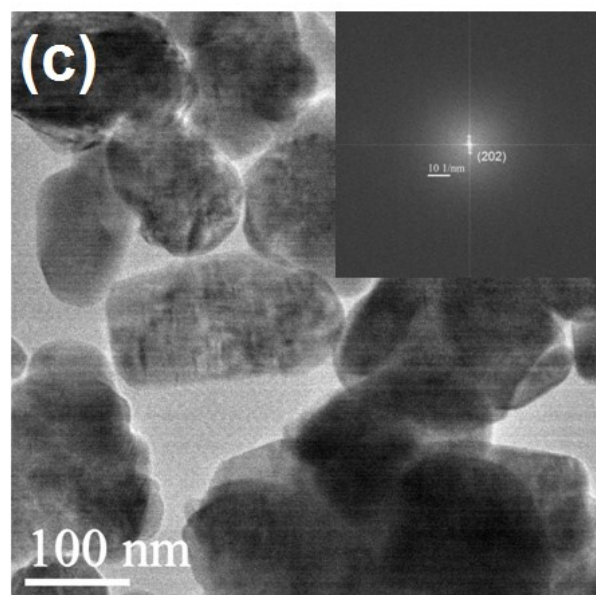
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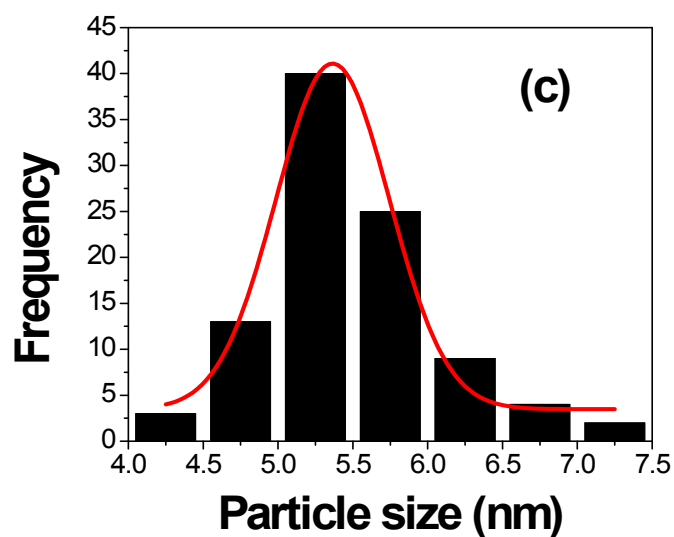
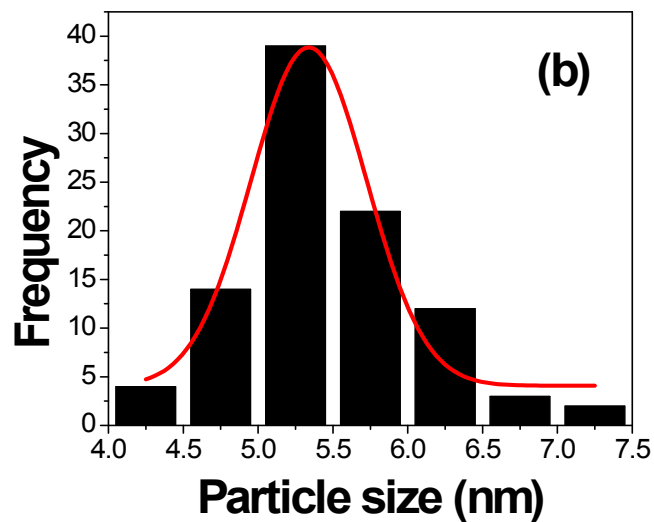
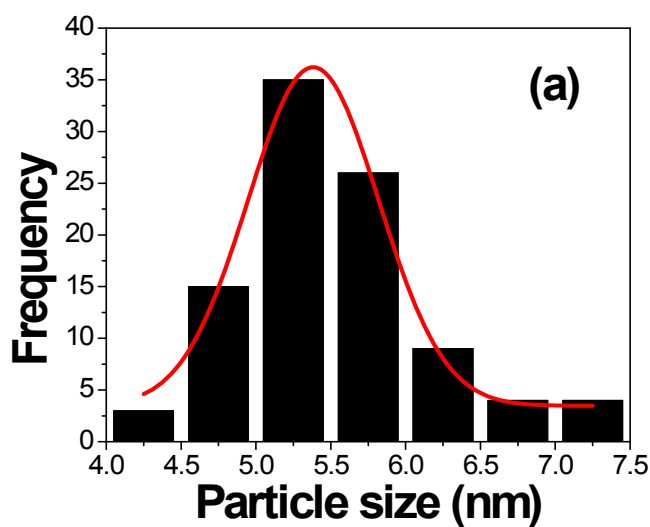
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S-1: TEM Images of (a) ZCF1, (b) ZCF2, (c) ZNC and their respective FFT plots in the inset

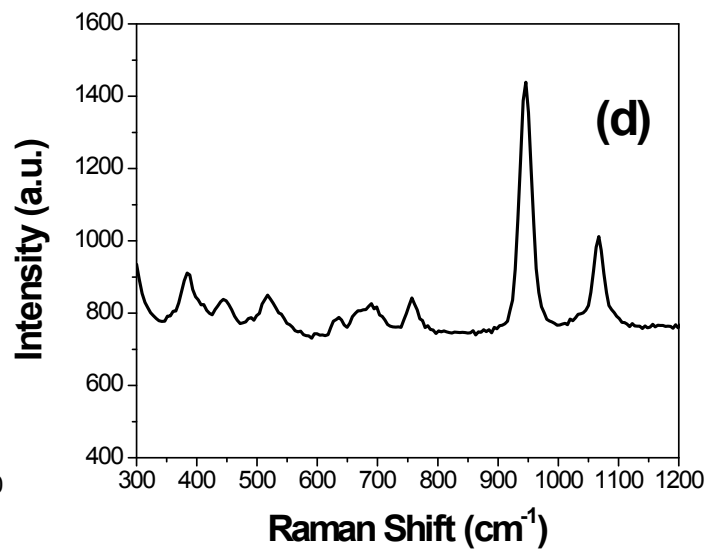
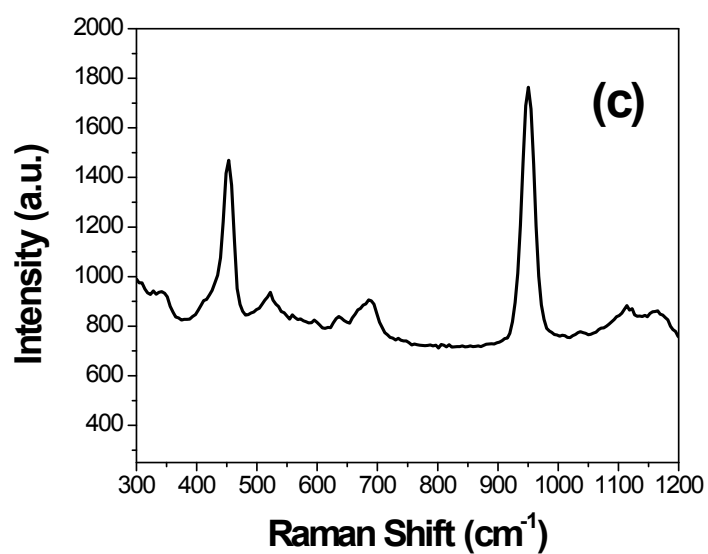
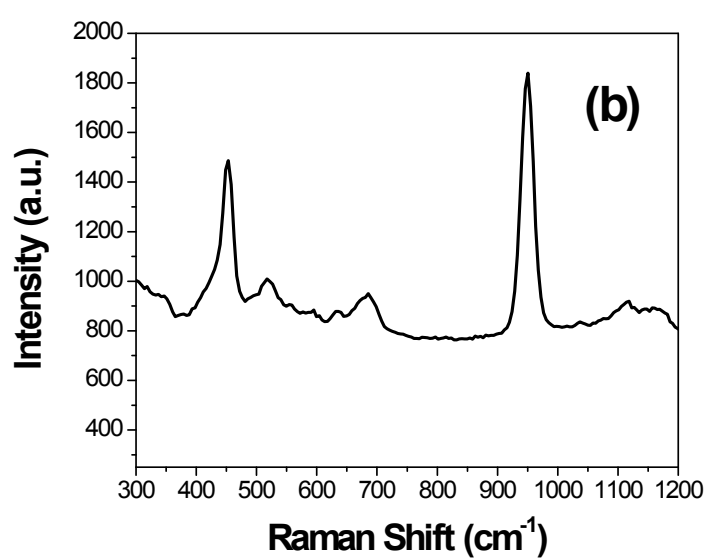
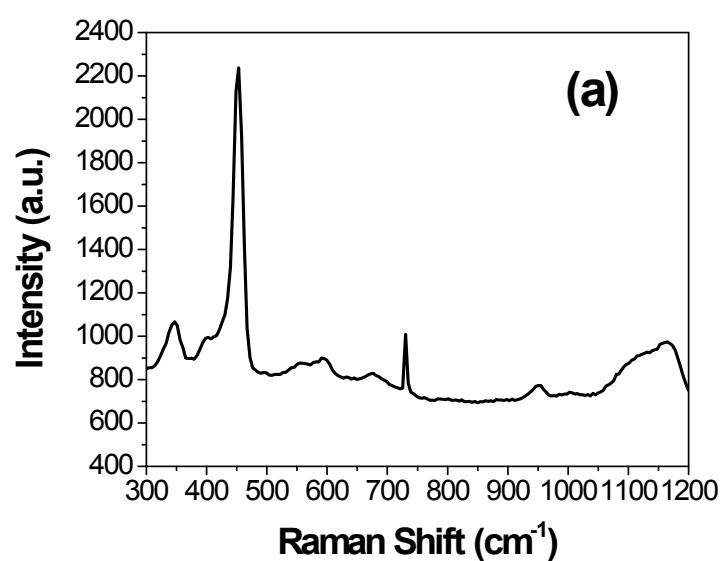




S-2: Particle Size Distribution Plots of (a) ZQD [mean particle diameter 5.38 ± 0.87 nm], (b) ZCF1 [mean particle diameter 5.41 ± 0.39 nm], (c) ZCF2 [mean particle diameter 5.56 ± 0.47 nm]



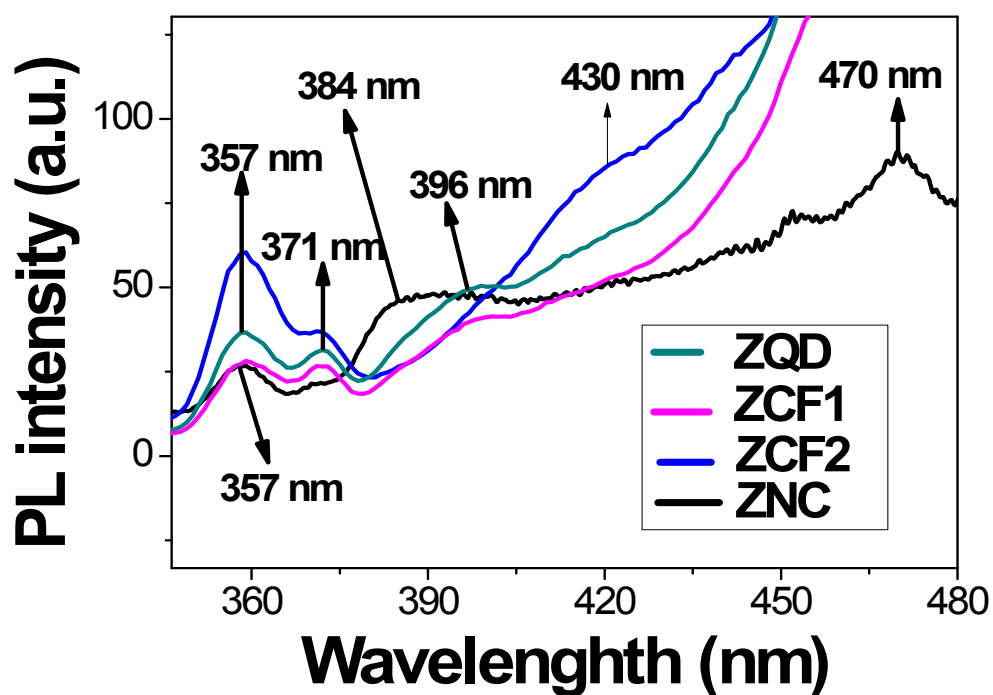
S-3: Raman Spectra of (a) ZNC, (b) ZQD, (c) ZCF1, (d) ZCF2



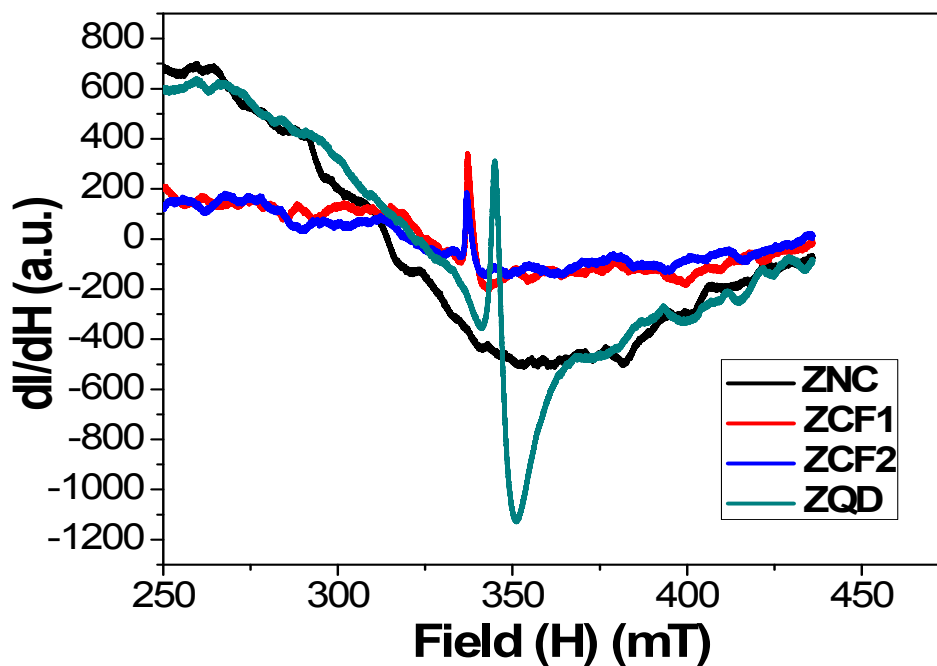
S-4: Raman peaks detected in the Spectrums of ZNC, ZQD, ZCF1 and ZCF2

ZQD (nm ⁻¹)	Assignment	ZCF1 (nm ⁻¹)	Assignment	ZCF2 (nm ⁻¹)	Assignment	ZNC (nm ⁻¹)	Assignment
345	E ₂ (high)- E ₂ (low)	345	E ₂ (high)- E ₂ (low)	384	E ₂ (high)- E ₂ (low)	345	E ₂ (high)- E ₂ (low)
-	-	-	-			400	A ₁ (TO)
451	Oxygen sublattice A ₁ (LO) mode	451	Oxygen sublattice A ₁ (LO) mode	444	Oxygen sublattice A ₁ (LO) mode	451	Non-polar vibrational mode of oxygen sublattice with E ₂ symmetry, fingerprint of wurzite crystal structure of ZnO.
518	Surface phonon mode	518	Surface phonon mode	518	Surface phonon mode	-	-
-	-	-	-	--	-	558	Surface phonon
583	A ₁ (LO)	583	A ₁ (LO)	-	-	593	A ₁ (LO)
685	Oxygen sublattice TA+LO mode	685	Oxygen sublattice TA+LO mode	685	TA+LO phonon mode	685	TA+LO phonon mode
-	-	-	-	-	-	729	Second order E _{2L} - B _{1H} phonon mode
1116	A ₁ (2LO)	1116	A ₁ (2LO)	-	-	1164	A ₁ (2LO)

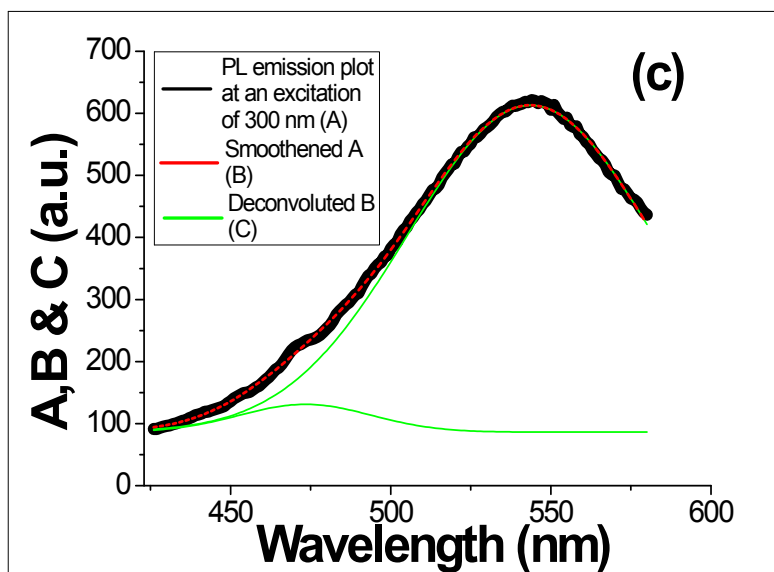
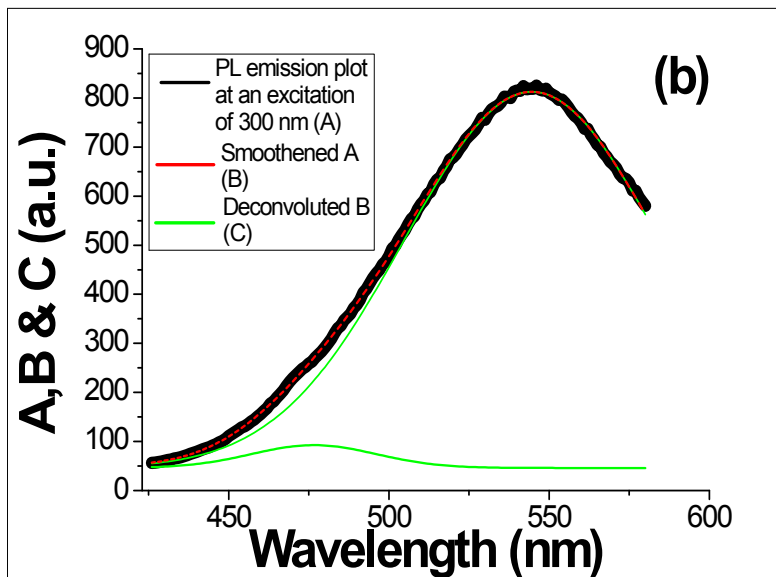
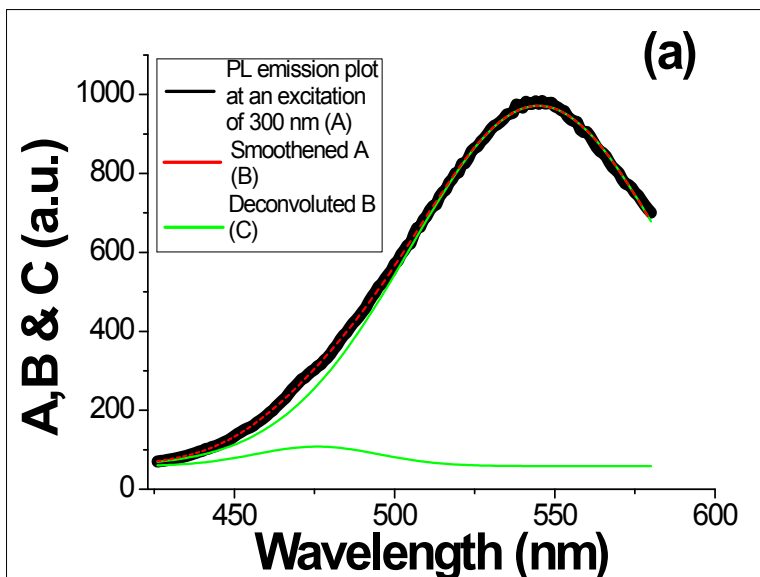
S-5: Near band gap PL emissions of ZQD, ZCF1, ZCF2, ZNC, ZNC2 powders excited at 4.1 eV.



S-6: EPR plot of ZQD, ZCF1, ZCF2, ZNC



S-7: (A) PL emissions plots of (a) ZQD, (b) ZCF1 and (c) ZCF2 fitted by Gaussian curve. In all cases the PL emission plots can be deconvoluted into two Gaussian curves: one peaked in the UV range and another peaked at 545 nm signifying green luminescence.



S-7(B): Configuration - coordinate diagram is generally used to describe the emission and absorption processes in solids. Here, the ground and excited electronic states, involved in the emission or absorption phenomenon, are described by classical quantum mechanical oscillators having quantum energy $\hbar\omega$ ^[1] i.e. the emission centres can have their own set of vibrational energy states which is $E_0 + n\hbar\omega$, where n is an integer and E_0 represents the ground state energy. Thus, their energy minima are displaced due to lattice vibration in the configuration coordinates.^[2] Therefore the broad emission spectra is consisted of various emission energy ranging from $E_T = E_D - (E_0 + n\hbar\omega)$, where E_D represents the energy corresponding to higher energy states. In fact, theoretical calculation predicts that the maximum of the emission typically occurs at an excited state for which $n \sim$ Huang – Rhys “S” factor. The significance of S is that it represents the strength of the electron-phonon interaction and it is calculated theoretically from half-width of the emission spectrum according to the following relation: ^[3, 4]

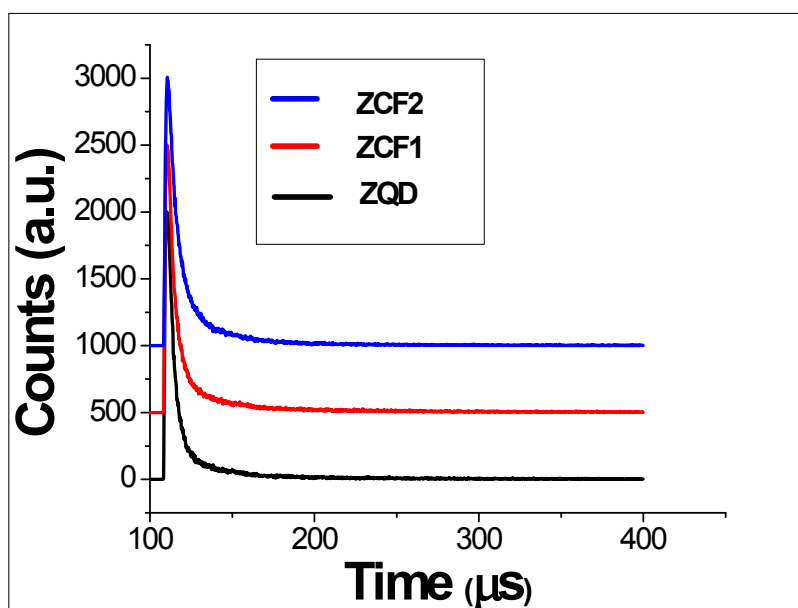
$$FWHM = 4(\ln 2)^{\frac{1}{2}}(kTS\hbar\omega)^{\frac{1}{2}}$$

On the otherhand, within the multi-phonon nonradiative, nonradiative relaxations of excited electrons are mediated by the excitation and emission of phonons and the corresponding rate (k_{nr}) is given by the following relation (3, 4):

$$k_{nr} = \frac{2\pi}{\hbar} [V_{ab}(R)]^2 \exp[-S(2\dot{\gamma})] I_p \left(2S[\dot{\gamma}(\dot{\gamma} + 1)]^{\frac{1}{2}} \right) [\dot{\gamma}(\dot{\gamma} + 1)]^{\frac{p}{2}}$$

where $\dot{\gamma}$ is the Bose thermal occupation of phonon mode $\hbar\omega$, p is the exothermicity expressed as integral number of vibrational quanta, I_p is a modified Bessel function. For further details please refer to Ref. 5.

S - 8: Decay plot of the PL emissions of ZQD, ZCF1, ZCF2 powders excited at 4.1 eV



S-9: Time resolved PL data for ZnO QD

Sample. Code	τ_1 (μ s)	$\tau_2(\mu$ s)	$\tau_3(\mu$ s)	$\tau_{avg}(\mu$ s)	B_1	B_2	B_3	Goodness of fit (χ)	intensity of PL w.r.t. :		
									τ_1	τ_2	τ_3
ZQD	3.99	22.01	112.7	26.00	2109.459	233.199	21.048	1.212	90.0	9.80	0.2
ZCF1	4.20	19.63	88.59	26.72	1988.201	290.611	41.823	1.135	85.7	12.5	1.8
ZCF2	5.19	19.37	57.74	18.33	1744.029	401.471	48.782	1.088	79.5	18.3	2.2

S-10: Standard deviation of the fitted data of S-9

<u>Sample. Code</u>	<u>Standard deviation in τ_1 ($10^{-2}\mu s$)</u>	<u>Standard deviation in τ_2 (μs)</u>	<u>Standard deviation in τ_3 (μs)</u>	<u>Standard deviation in B_1</u>	<u>Standard deviation in B_2</u>	<u>Standard deviation in B_3</u>
<u>ZQD</u>	<u>5.42</u>	<u>1.11</u>	<u>27.05</u>	<u>18.52</u>	<u>8.63</u>	<u>4.11</u>
<u>ZCF1</u>	<u>7.13</u>	<u>1.10</u>	<u>10.34</u>	<u>20.45</u>	<u>13.88</u>	<u>5.81</u>
<u>ZCF2</u>	<u>1.17</u>	<u>1.28</u>	<u>7.16</u>	<u>27.85</u>	<u>21.04</u>	<u>14.04</u>

S- 11: Justification for assigning τ_1 and τ_2 to nonradiative and radiative recombination:

Defect sites act as a source of non-radiative recombination centre i.e. samples with large defect concentration possesses higher decay probability of photo-generated charge carriers via nonradiative decay path rather than radiative decay path.^[6] Here, we are examining the decay process of green emission that originates due to electronic transition between singly charged oxygen vacancy (V_o^\cdot) to zinc vacancy (V_{zn}) sites i.e. we are considering decay process involving defect sites. Thus non-radiative decay is ascribed to be predominant here. If we compare the proportion of the decay processes corresponding to τ_1 and τ_2 , it may be observed that percentage of the decay process corresponding to τ_1 is very high i.e. decay process involving τ_1 may be attributed to be non-radiative in nature. As discussed in the manuscript, the defect sites that causes the transition are deep level defect sites, thus we have ascribed them as shallow trapped electrons and shallow trapped holes. The effect of electron - phonon interaction is also observed from the variation of $A_1(2LO)/A_1(LO)$. It decreases with increasing time, same trend is observed for FWHM of emission spectra.

References:

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